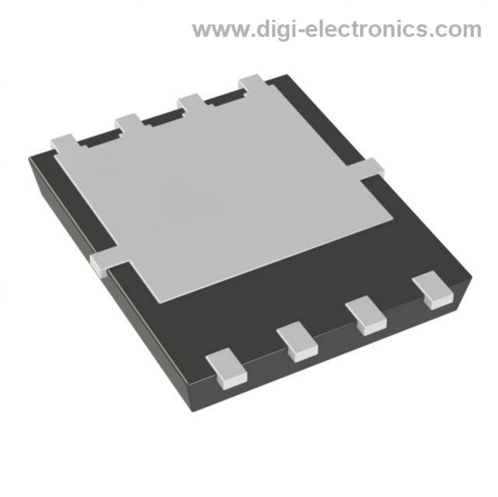
AON6206 Datasheet



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DiGi Electronics Part Number	AON6206-DG
Manufacturer	Alpha & Omega Semiconductor Inc.
Manufacturer Product Number	AON6206
Description	MOSFET N-CH 30V 20A/24A 8DFN
Detailed Description	N-Channel 30 V 20A (Ta), 24A (Tc) 4.2W (Ta), 31W (Tc) Surface Mount 8-DFN (5x6)

Purchase and inquiry

Manufacturer Product Number:	AON6206	Manufacturer:	Alpha & Omega Semiconductor Inc.
Series:	-	Product Status:	Obsolete
FET Type:	N-Channel	Technology:	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	30 V	Current - Continuous Drain (Id) @ 25°C:	20A (Ta), 24A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	4.5V, 10V	Rds On (Max) @ Id, Vgs:	6.5mOhm @ 20A, 10V
Vgs(th) (Max) @ Id:	2.3V @ 250µA	Gate Charge (Qg) (Max) @ Vgs:	23.5 nC @ 10 V
Vgs (Max):	±20V	Input Capacitance (Ciss) (Max) @ Vds:	1670 pF @ 15 V
FET Feature:	-	Power Dissipation (Max):	4.2W (Ta), 31W (Tc)
Operating Temperature:	-55°C ~ 150°C (TJ)	Mounting Type:	Surface Mount
Supplier Device Package:	8-DFN (5x6)	Package / Case:	8-PowerSMD, Flat Leads
Base Product Number:	AON62		

Environmental & Export classification

Moisture Sensitivity Level (MSL):	1 (Unlimited)	REACH Status:	REACH Unaffected
ECCN:	EAR99	HTSUS:	8541.29.0095

ALPHA & OMEGA
SEMICONDUCTOR

AON6206

30V N-Channel MOSFET

General Description

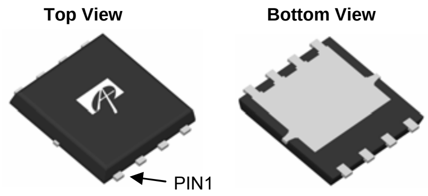
The AON6206 uses trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance.Power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and C_{rss}.In addition,switching behavior is well controlled with a "Schottky style" soft recovery body diode.

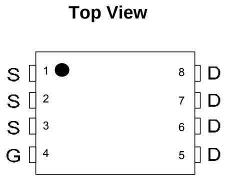
Product Summary

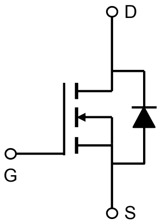
V_{DS}	30V
I_D (at V_{GS}=10V)	24A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 6.5mΩ
$R_{DS(ON)}$ (at V_{GS} = 4.5V)	< 9mΩ

100% UIS Tested
100% R_g Tested

DFN5X6







Absolute Maximum Ratings T_A=25°C unless otherwise noted				
Parameter		**Symbol**	**Maximum**	**Units**
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [G]	T_C=25°C	I_D	24	A
	T_C=100°C		19	
Pulsed Drain Current [C]		I_{DM}	150	
Continuous Drain Current	T_A=25°C	I_{DSM}	20	A
	T_A=70°C		16	
Avalanche Current [C]		I_{AS}, I_{AR}	30	A
Avalanche energy L=0.1mH [C]		E_{AS}, E_{AR}	45	mJ
Power Dissipation [B]	T_C=25°C	P_D	31	W
	T_C=100°C		12	
Power Dissipation [A]	T_A=25°C	P_{DSM}	4.2	W
	T_A=70°C		2.7	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics					
Parameter		**Symbol**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	25	30	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		55	65	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	3	4	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	μA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250μA	1.3	1.8	2.3	V
$I_{D(ON)}$	On state drain current	V_{GS}=10V, V_{DS}=5V	150			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		5.2	6.5	mΩ
		T_J=125°C		7.7	9.5	
		V_{GS}=4.5V, I_D=15A		7	9	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		70		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.7	1	V
I_S	Maximum Body-Diode Continuous Current				40	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz	1110	1390	1670	pF
C_{oss}	Output Capacitance		350	510	670	pF
C_{rss}	Reverse Transfer Capacitance		32	53	90	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.4	0.9	1.5	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=20A	15.5	19.6	23.5	nC
Q_g(4.5V)	Total Gate Charge		7	8.7	10.5	nC
Q_{gs}	Gate Source Charge		2.8	3.6	4.5	nC
Q_{gd}	Gate Drain Charge		1.8	3	4.2	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω		7.5		ns
t_r	Turn-On Rise Time			9.7		ns
$t_{D(off)}$	Turn-Off DelayTime			20		ns
t_f	Turn-Off Fall Time			4.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=500A/μs	12	15	18	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=500A/μs	30	37	45	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on R $_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

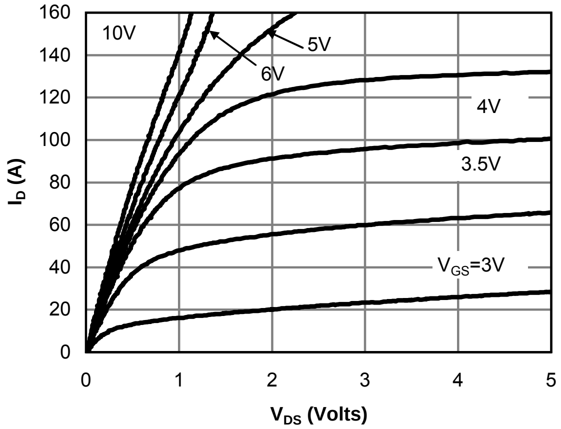


Fig 1: On-Region Characteristics (Note E)

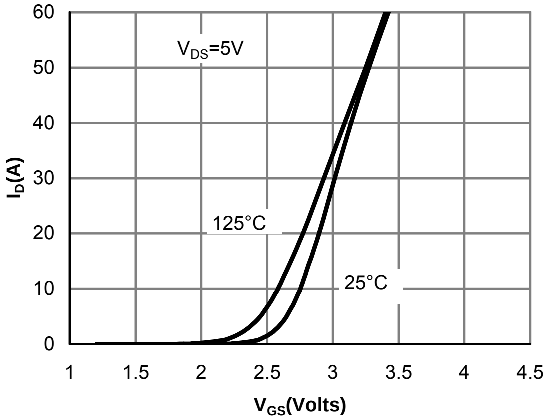


Figure 2: Transfer Characteristics (Note E)

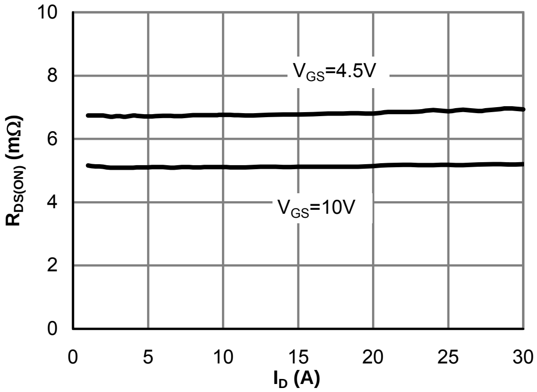


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

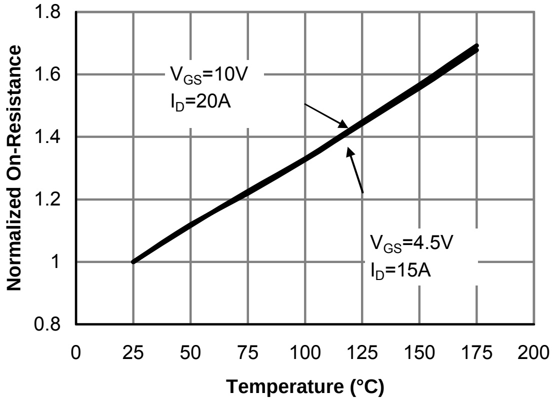


Figure 4: On-Resistance vs. Junction Temperature (Note E)

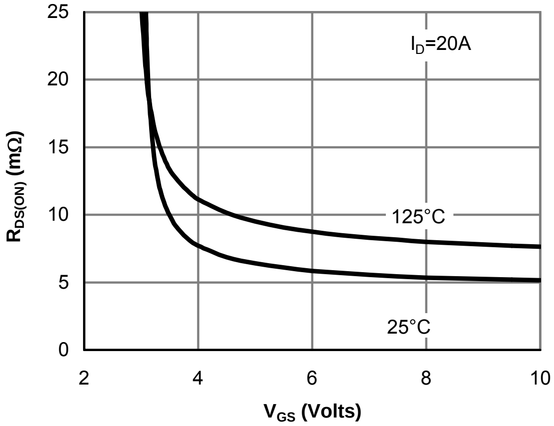


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

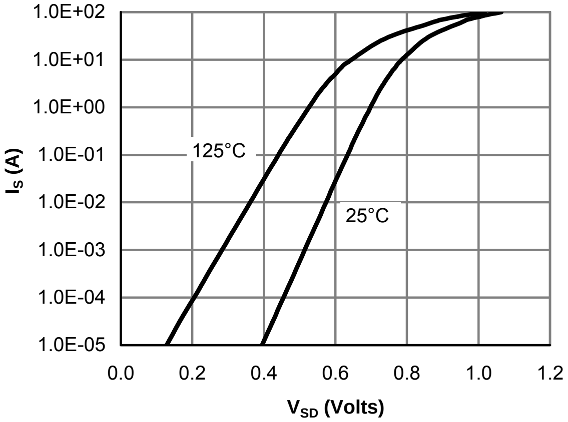


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

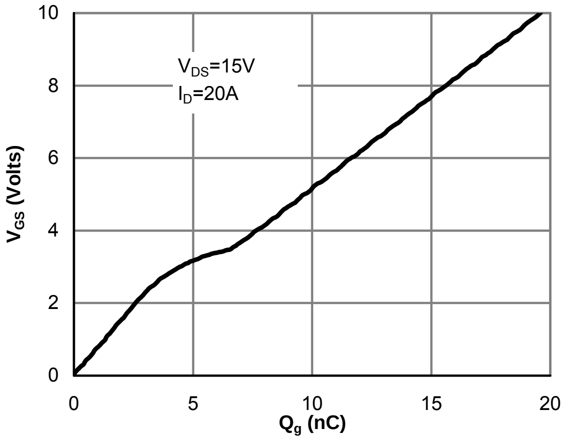


Figure 7: Gate-Charge Characteristics

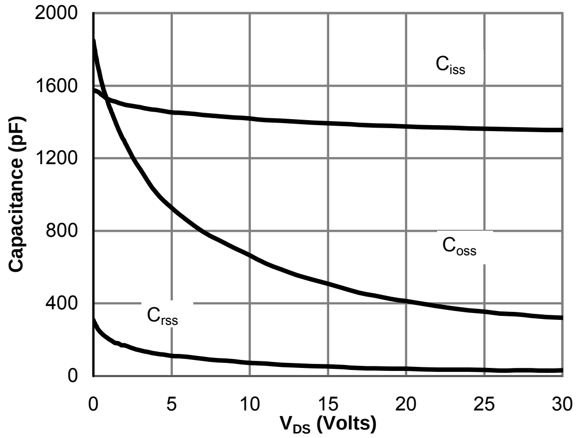


Figure 8: Capacitance Characteristics

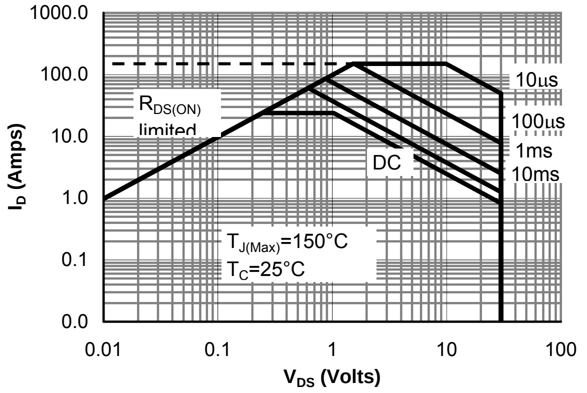


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

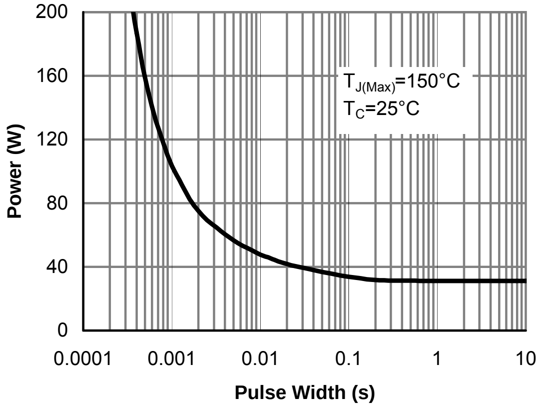


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

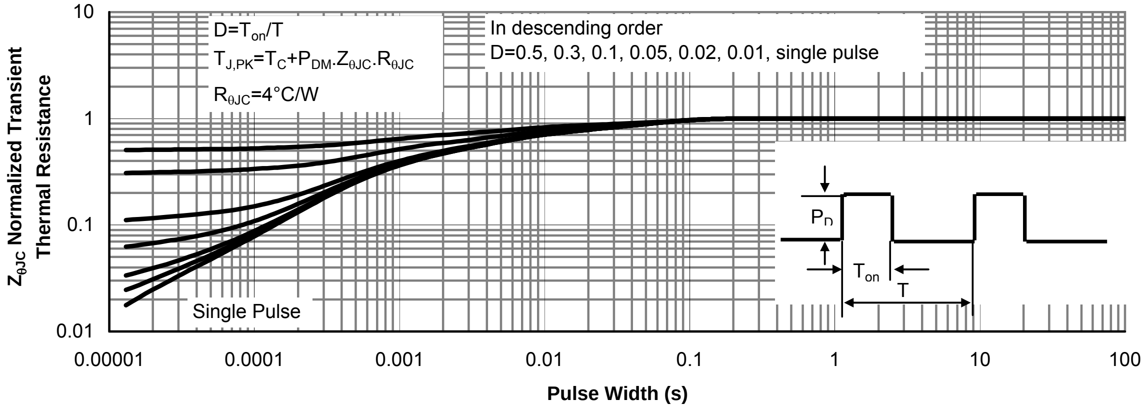


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

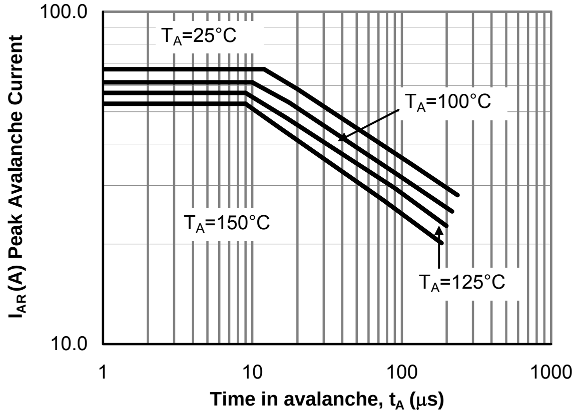


Figure 12: Single Pulse Avalanche capability (Note C)

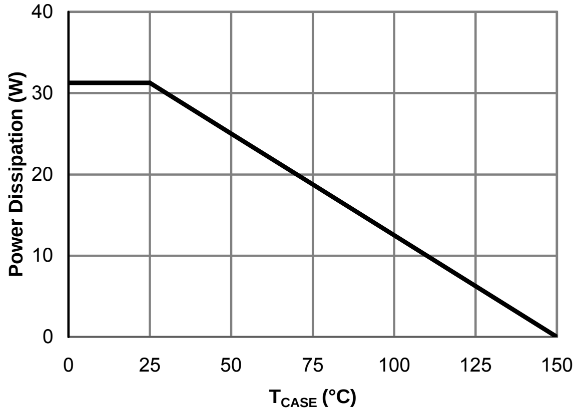


Figure 13: Power De-rating (Note F)

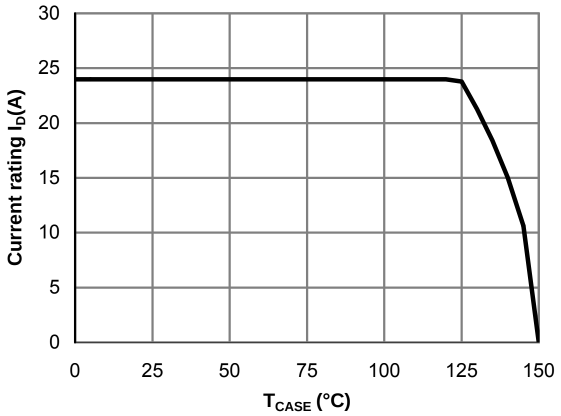


Figure 14: Current De-rating (Note F)

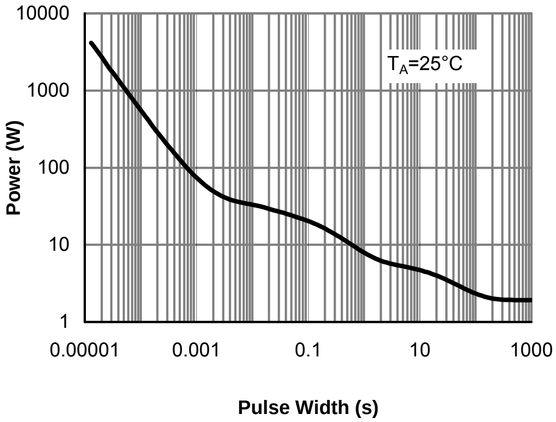


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

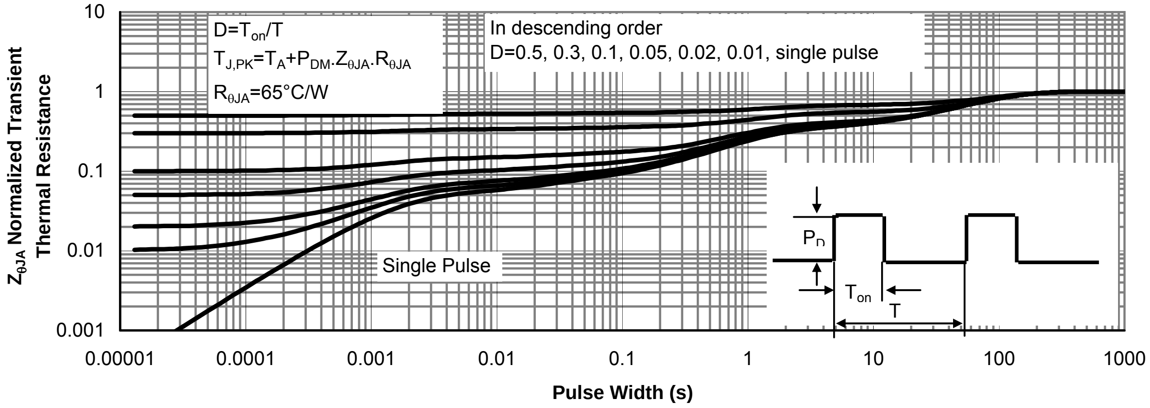
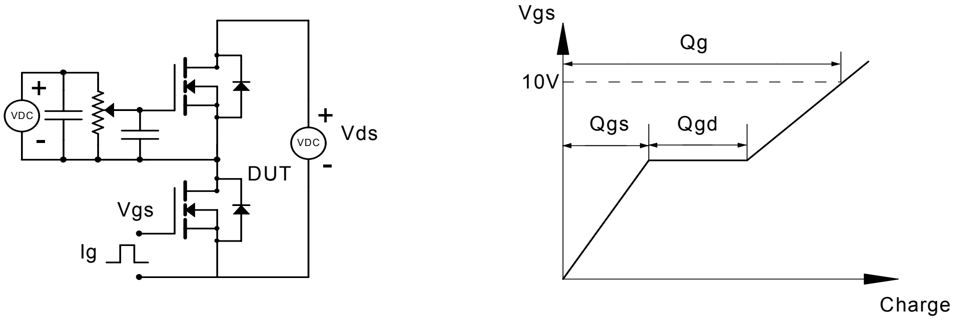
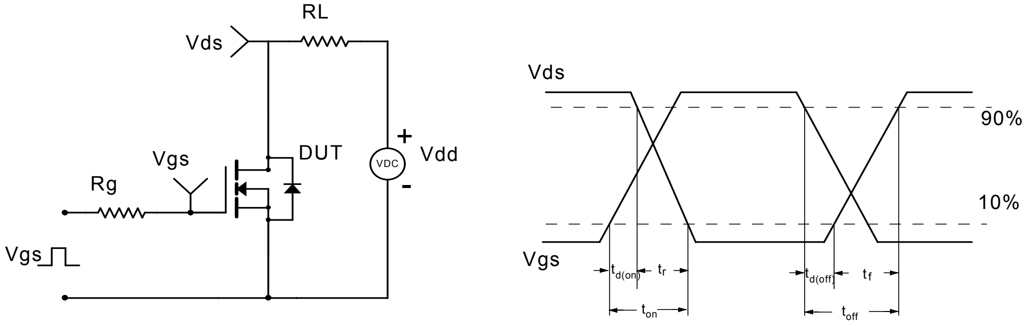


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

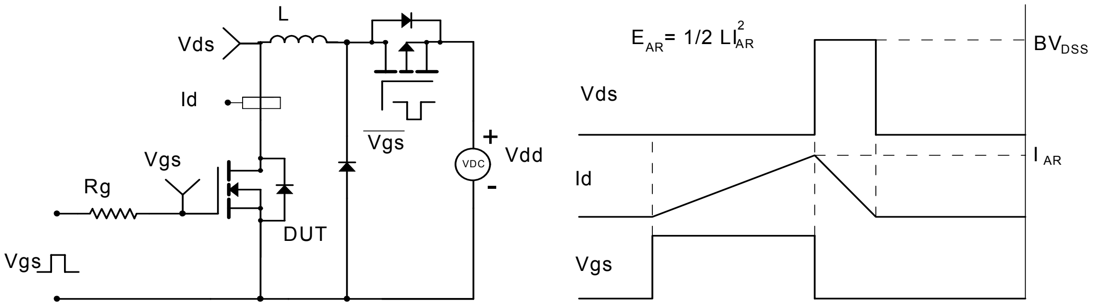
Gate Charge Test Circuit & Waveform



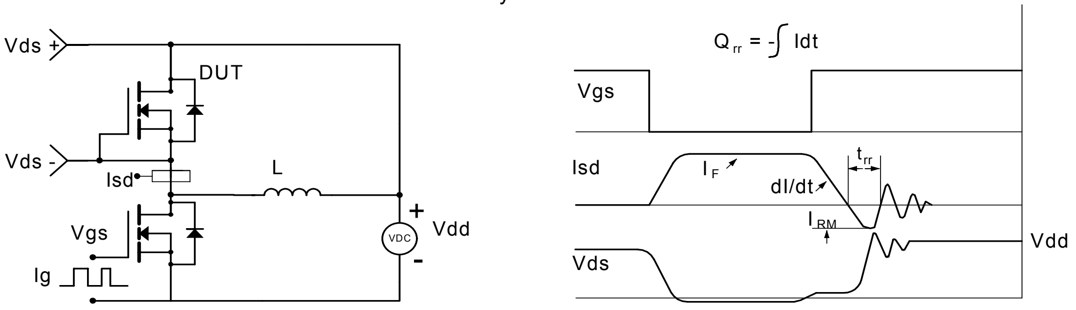
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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CERTIFICATE OF INCORPORATION

I hereby certify that

is this day incorporated in Hong Kong under the Companies Ordinance (Chapter 622 of the Laws of Hong Kong), and that this company is a limited company.

Registrar of Companies

Hong Kong Special Administrative Region

ASA

MEMBERSHIP

Certificate

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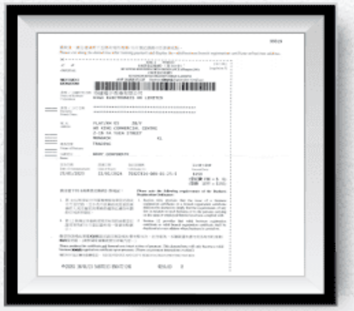

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